# IPB029N06N3G-VB Datasheet

## N-Channel 60 V (D-S) MOSFET

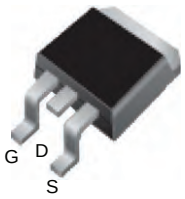
| PRODUCT SUMMARY | |
|---|---|
| $V_{DS}$ (V) | 60 |
| $R_{DS(on)}$ (Ω) at $V_{GS}$ = 10 V | 0.0028 |
| $R_{DS(on)}$ (Ω) at $V_{GS}$ = 4.5 V | 0.0120 |
| $I_D$ (A) | 210 |
| Configuration | Single |

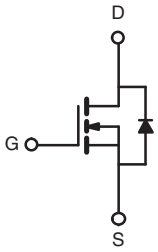
### FEATURES

- **Halogen-free According to IEC 61249-2-21 Definition**
- Trench Power MOSFET
- Package with Low Thermal Resistance
- 100 % $R_g$ and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

RoHS COMPLIANT
HALOGEN FREE

**D²PAK (TO-263)**




N-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS ($T_C$ = 25 °C, unless otherwise noted) | | | | |
|---|---|---|---|---|
| **PARAMETER** | | **SYMBOL** | **LIMIT** | **UNIT** |
| Drain-Source Voltage | | $V_{DS}$ | 60 | V |
| Gate-Source Voltage | | $V_{GS}$ | ± 20 | |
| Continuous Drain Current | $T_C$ = 25 °C | $I_D$ | 210 | A |
| | $T_C$ = 125 °C | | 120 [a] | |
| Continuous Source Current (Diode Conduction)[a] | | $I_S$ | 120 [a] | |
| Pulsed Drain Current[b] | | $I_{DM}$ | 480 | |
| Single Pulse Avalanche Current | L = 0.1 mH | $I_{AS}$ | 75 | |
| Single Pulse Avalanche Energy | | $E_{AS}$ | 281 | mJ |
| Maximum Power Dissipation[b] | $T_C$ = 25 °C | $P_D$ | 375 | W |
| | $T_C$ = 125 °C | | 125 | |
| Operating Junction and Storage Temperature Range | | $T_J$, $T_{stg}$ | - 55 to + 175 | °C |

| THERMAL RESISTANCE RATINGS | | | | |
|---|---|---|---|---|
| **PARAMETER** | | **SYMBOL** | **LIMIT** | **UNIT** |
| Junction-to-Ambient | PCB Mount[c] | $R_{thJA}$ | 40 | °C/W |
| Junction-to-Case (Drain) | | $R_{thJC}$ | 0.4 | |

**Notes**

a. Package limited.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
c. When mounted on 1" square PCB (FR-4 material).
d. Parametric verification ongoing.

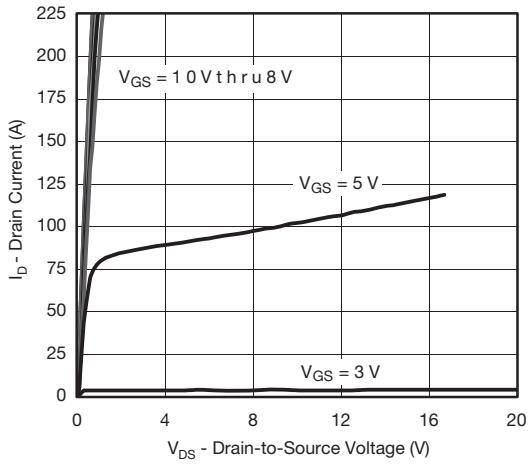
| **SPECIFICATIONS** ($T_C$ = 25 °C, unless otherwise noted) | | | | | | | |
|---|---|---|---|---|---|---|---|
| **PARAMETER** | **SYMBOL** | **TEST CONDITIONS** | | **MIN.** | **TYP.** | **MAX.** | **UNIT** |
| **Static** | | | | | | | |
| Drain-Source Breakdown Voltage | $V_{DS}$ | $V_{GS}$ = 0, $I_D$ = 250 µA | | 60 | - | - | V |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_D$ = 250 µA | | 2.0 | | 4.0 | |
| Gate-Source Leakage | $I_{GSS}$ | $V_{DS}$ = 0 V, $V_{GS}$ = ± 20 V | | - | - | ± 100 | nA |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{GS}$ = 0 V | $V_{DS}$ = 60 V | - | - | 1.0 | µA |
| | | $V_{GS}$ = 0 V | $V_{DS}$ = 60 V, $T_J$ = 125 °C | - | - | 50 | |
| | | $V_{GS}$ = 0 V | $V_{DS}$ = 60 V, $T_J$ = 175 °C | - | - | 350 | |
| On-State Drain Current[a] | $I_{D(on)}$ | $V_{GS}$ = 10 V | $V_{DS}$ ≥ 5 V | 120 | - | - | A |
| Drain-Source On-State Resistance[a] | $R_{DS(on)}$ | $V_{GS}$ = 10 V | $I_D$ = 30 A | - | 0.0028 | - | Ω |
| | | $V_{GS}$ = 10 V | $I_D$ = 30 A, $T_J$ = 125 °C | - | 0.0060 | - | |
| | | $V_{GS}$ = 10 V | $I_D$ = 30 A, $T_J$ = 175 °C | - | 0.0080 | - | |
| | | $V_{GS}$ = 4.5 V | $I_D$ = 20 A | - | 0.012 | - | |
| Forward Transconductance[b] | $g_{fs}$ | $V_{DS}$ = 15 V, $I_D$ = 30 A | | - | 109 | - | S |
| **Dynamic[b]** | | | | | | | |
| Input Capacitance | $C_{iss}$ | $V_{GS}$ = 0 V | $V_{DS}$ = 25 V, f = 1 MHz | - | 7300 | 9125 | pF |
| Output Capacitance | $C_{oss}$ | | | - | 935 | 1170 | |
| Reverse Transfer Capacitance | $C_{rss}$ | | | - | 647 | 810 | |
| Total Gate Charge[c] | $Q_g$ | $V_{GS}$ = 10 V | $V_{DS}$ = 30 V, $I_D$ = 110 A | - | 184 | 276 | nC |
| Gate-Source Charge[c] | $Q_{gs}$ | | | - | 24.7 | - | |
| Gate-Drain Charge[c] | $Q_{gd}$ | | | - | 50.4 | - | |
| Gate Resistance | $R_g$ | f = 1 MHz | | 0.5 | 1.1 | 1.6 | Ω |
| Turn-On Delay Time[c] | $t_{d(on)}$ | $V_{DD}$ = 30 V, $R_L$ = 0.27 Ω<br>$I_D$ ≅ 110 A, $V_{GEN}$ = 10 V, $R_g$ = 2.5 Ω | | - | 19 | 29 | ns |
| Rise Time[c] | $t_r$ | | | - | 23 | 35 | |
| Turn-Off Delay Time[c] | $t_{d(off)}$ | | | - | 83 | 125 | |
| Fall Time[c] | $t_f$ | | | - | 35 | 53 | |
| **Source-Drain Diode Ratings and Characteristics[b]** | | | | | | | |
| Pulsed Current[a] | $I_{SM}$ | | | - | - | 480 | A |
| Forward Voltage | $V_{SD}$ | $I_F$ = 100 A, $V_{GS}$ = 0 | | - | 0.9 | 1.5 | V |

**Notes**

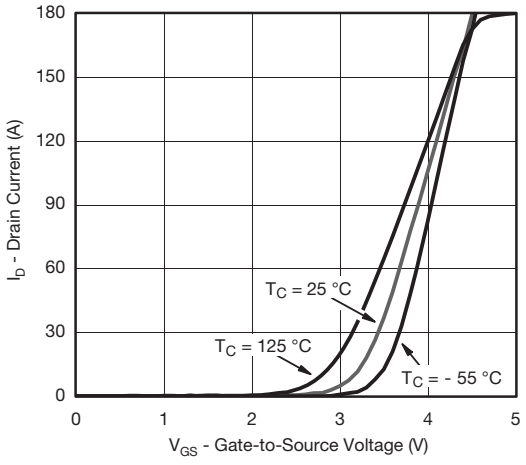
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

*Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*

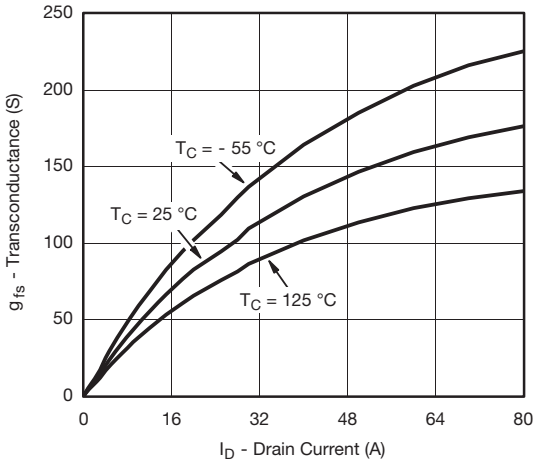
**TYPICAL CHARACTERISTICS** ($T_A$ = 25 °C, unless otherwise noted)



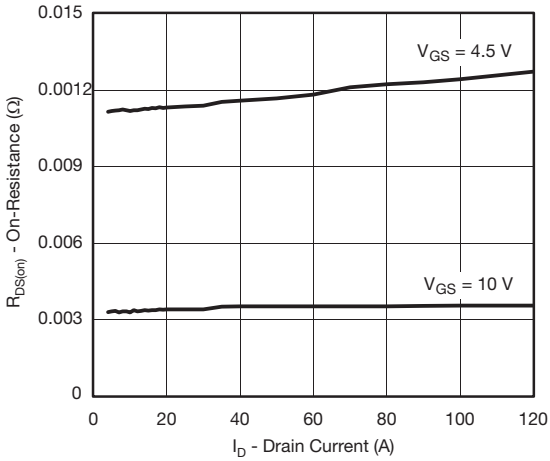

**Output Characteristics**



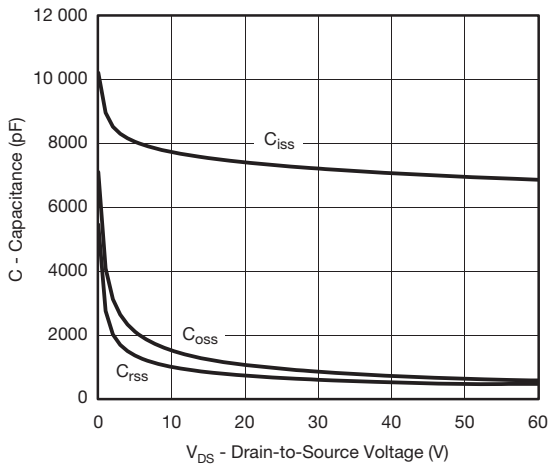

**Transfer Characteristics**



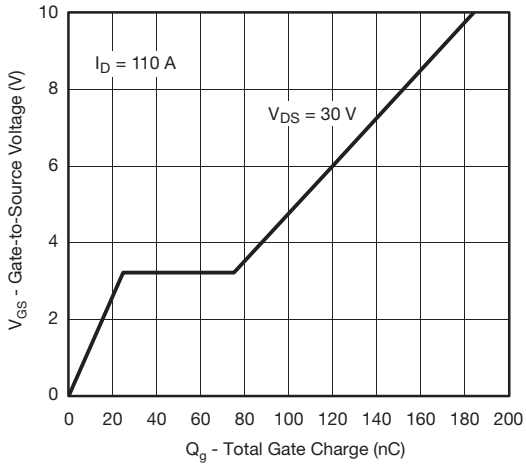

**Transconductance**




**On-Resistance vs. Drain Current**

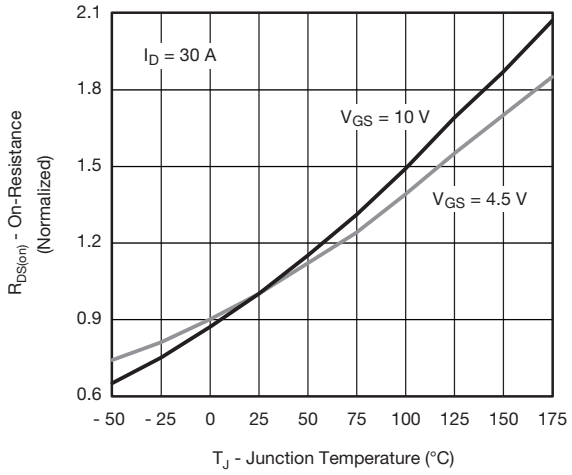



**Capacitance**

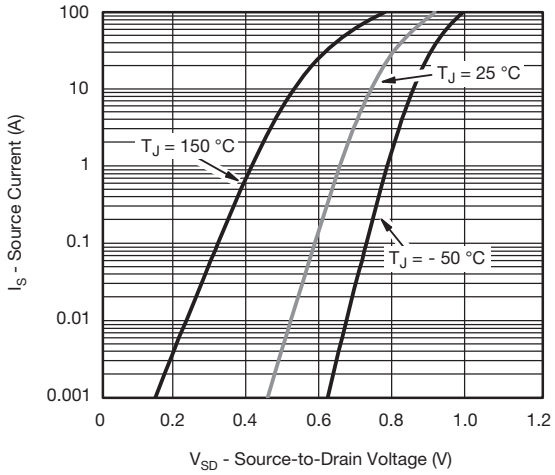



**Gate Charge**

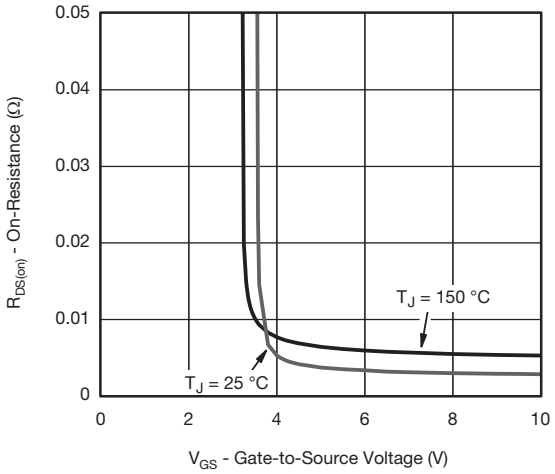
**TYPICAL CHARACTERISTICS** ($T_A$ = 25 °C, unless otherwise noted)



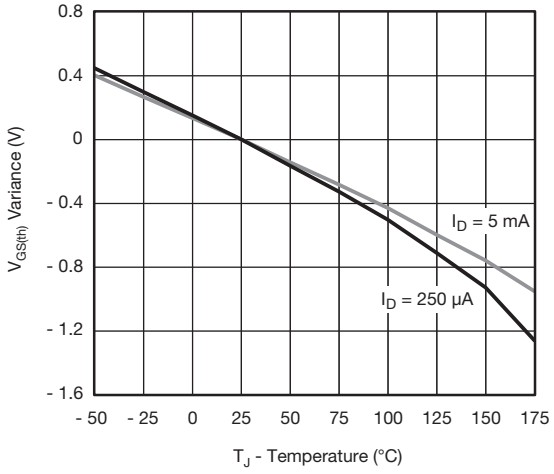

**On-Resistance vs. Junction Temperature**



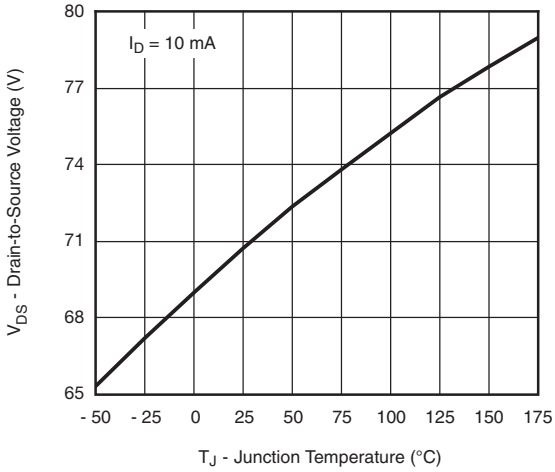

**Source Drain Diode Forward Voltage**




**On-Resistance vs. Gate-to-Source Voltage**

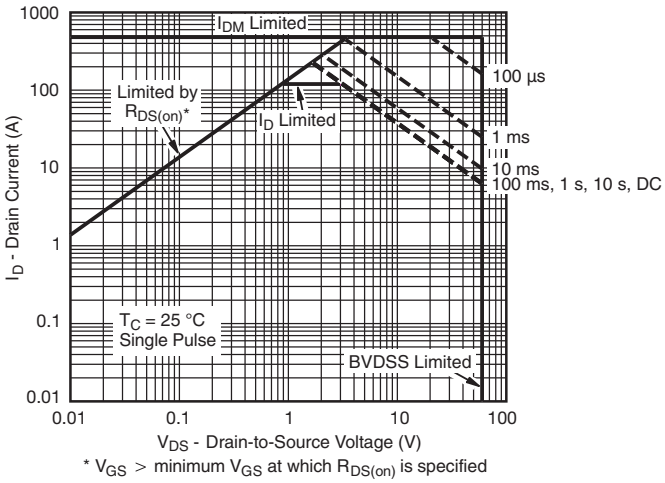



**Threshold Voltage**

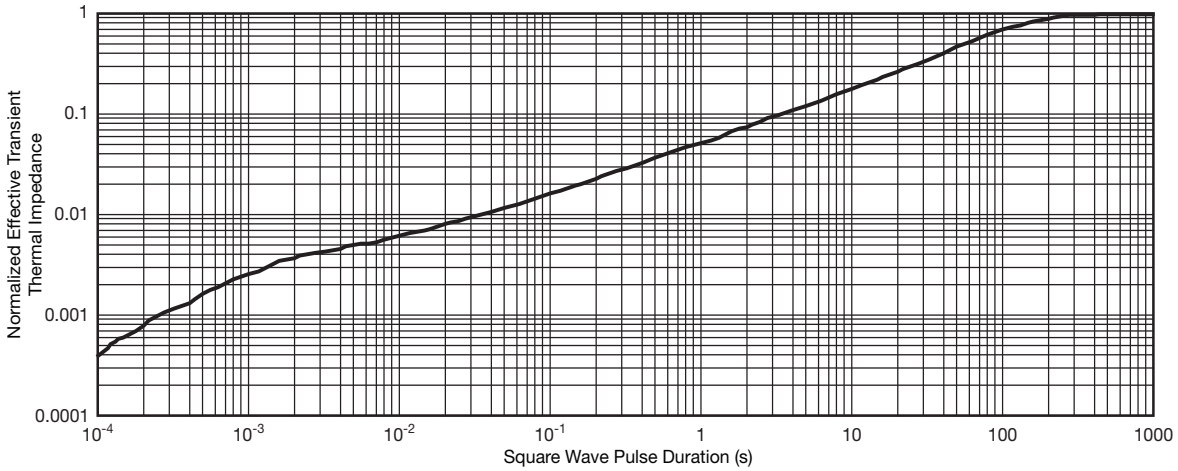



**Drain Source Breakdown vs. Junction Temperature**

**THERMAL RATINGS** ($T_A$ = 25 °C, unless otherwise noted)

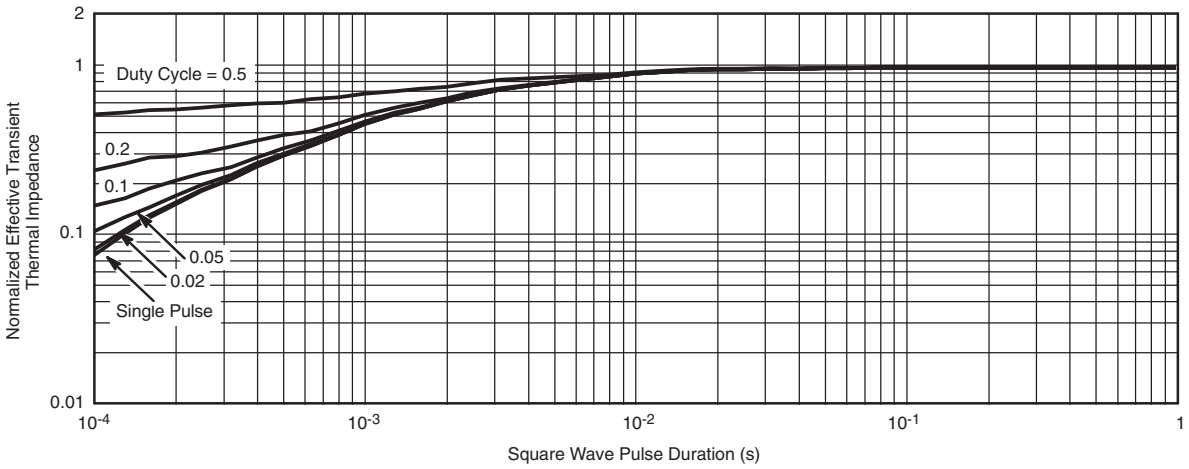



**Safe Operating Area**




**Normalized Thermal Transient Impedance, Junction-to-Ambient**

**THERMAL RATINGS** ($T_A$ = 25 °C, unless otherwise noted)



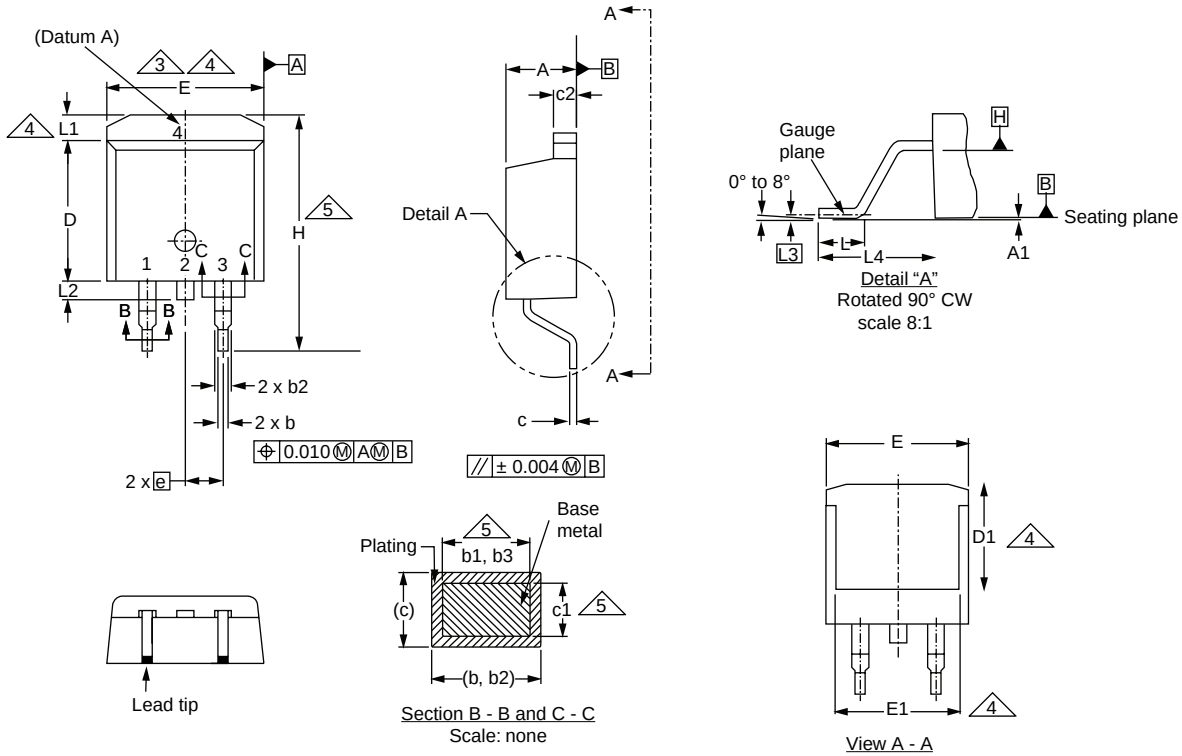

**Normalized Thermal Transient Impedance, Junction-to-Case**

**Note**

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

  are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

## TO-263AB




| | MILLIMETERS | | INCHES | |
|---|---|---|---|---|
| DIM. | MIN. | MAX. | MIN. | MAX. |
| A | 4.06 | 4.83 | 0.160 | 0.190 |
| A1 | 0.00 | 0.25 | 0.000 | 0.010 |
| b | 0.51 | 0.99 | 0.020 | 0.039 |
| b1 | 0.51 | 0.89 | 0.020 | 0.035 |
| b2 | 1.14 | 1.78 | 0.045 | 0.070 |
| b3 | 1.14 | 1.73 | 0.045 | 0.068 |
| c | 0.38 | 0.74 | 0.015 | 0.029 |
| c1 | 0.38 | 0.58 | 0.015 | 0.023 |
| c2 | 1.14 | 1.65 | 0.045 | 0.065 |
| D | 8.38 | 9.65 | 0.330 | 0.380 |

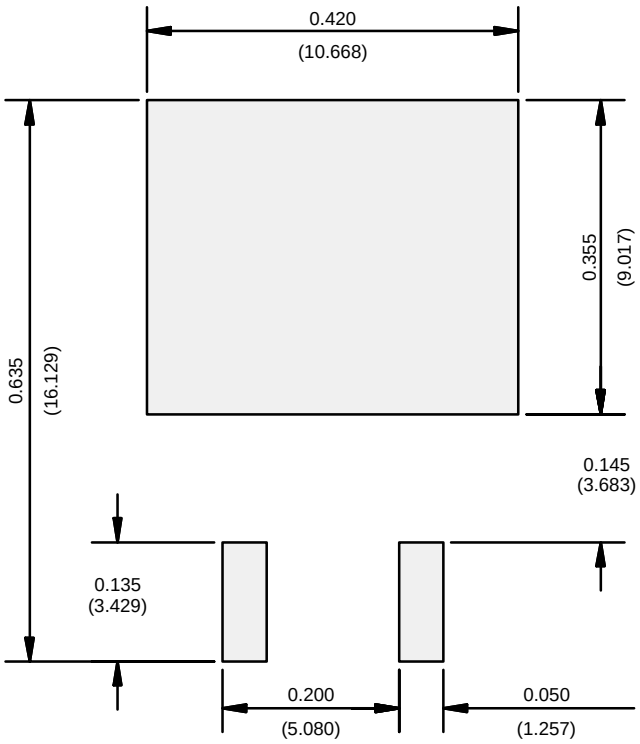
| | MILLIMETERS | | INCHES | |
|---|---|---|---|---|
| DIM. | MIN. | MAX. | MIN. | MAX. |
| D1 | 6.86 | - | 0.270 | - |
| E | 9.65 | 10.67 | 0.380 | 0.420 |
| E1 | 6.22 | - | 0.245 | - |
| e | 2.54 BSC | | 0.100 BSC | |
| H | 14.61 | 15.88 | 0.575 | 0.625 |
| L | 1.78 | 2.79 | 0.070 | 0.110 |
| L1 | - | 1.65 | - | 0.066 |
| L2 | - | 1.78 | - | 0.070 |
| L3 | 0.25 BSC | | 0.010 BSC | |
| L4 | 4.78 | 5.28 | 0.188 | 0.208 |

ECN: S-82110-Rev. A, 15-Sep-08
DWG: 5970

**Notes**

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.

## RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead




Recommended Minimum Pads
Dimensions in Inches/(mm)

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